

RJK0635DSP

60V, 3.5A, 98mΩ max.
N Channel Power MOS FET
Power Switching

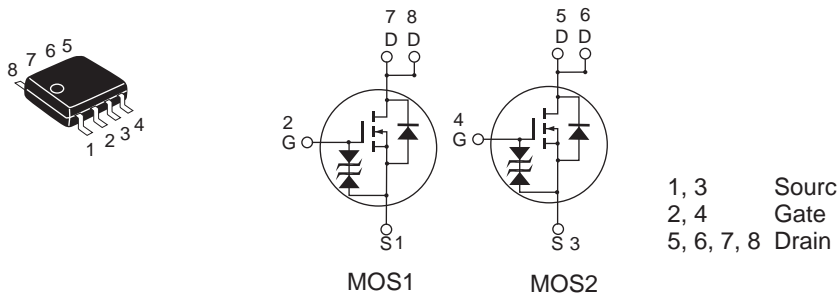
R07DS1345EJ0301
Rev.3.01
Nov.24.2016

Features

- Capable of 2.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
- Pb-free

Outline

RENESAS Package code: PRSP0008DD-D
(Package name: SOP-8<FP-8DAV>)



Absolute Maximum Ratings

(Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|----------------------------------------|----------------------------------------|-------------|------|
| Drain to source voltage | V _{DSS} | 60 | V |
| Gate to source voltage | V _{GSS} | ±12 | V |
| Drain current | I _D | 3.5 | A |
| Drain peak current | I _{D(pulse)} ^{Note1} | 14 | A |
| Body-drain diode reverse drain current | I _{DR} | 3.5 | A |
| Avalanche current | I _{AP} ^{Note 2} | 3.5 | A |
| Avalanche energy | E _{AS} ^{Note 2} | 1.05 | mJ |
| Channel dissipation | P _{ch} ^{Note3} | 1.2 | W |
| Channel dissipation | P _{ch} ^{Note4} | 1.8 | W |
| Channel temperature | T _{ch} | 150 | °C |
| Storage temperature | T _{stg} | -55 to +150 | °C |

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. Value at T_{ch} = 25°C, R_g ≥ 50 Ω

3. 1 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW ≤ 10s

4. 2 Drive operation : When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW ≤ 10s

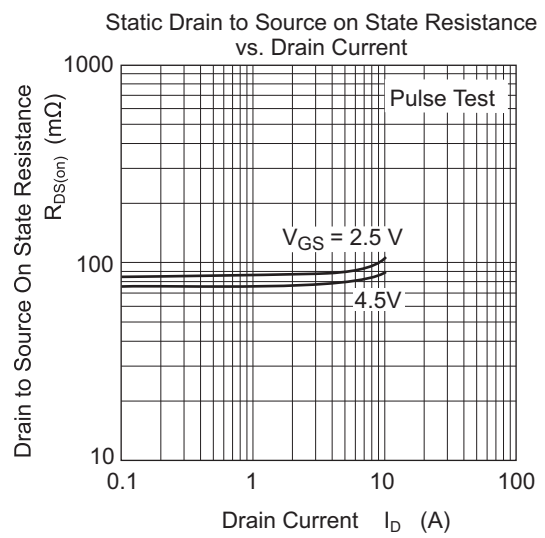
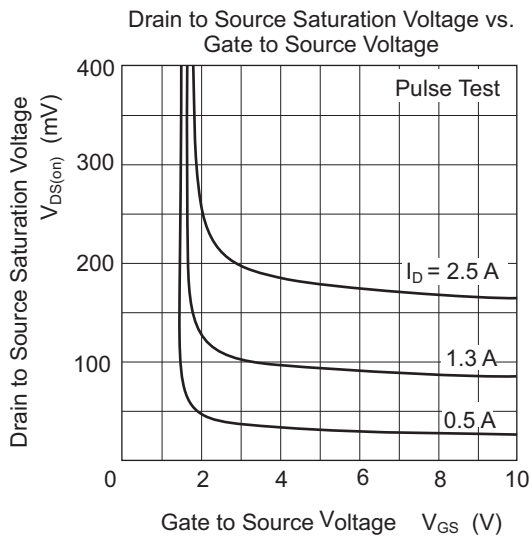
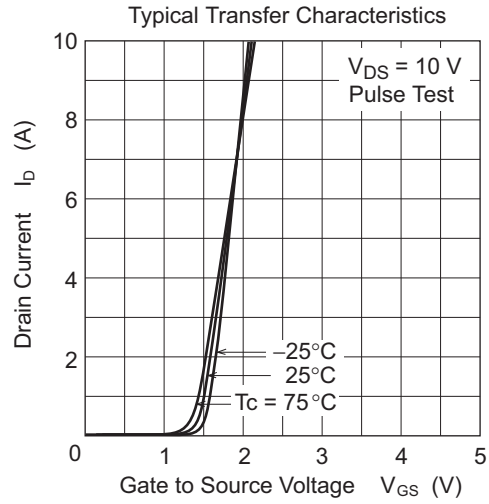
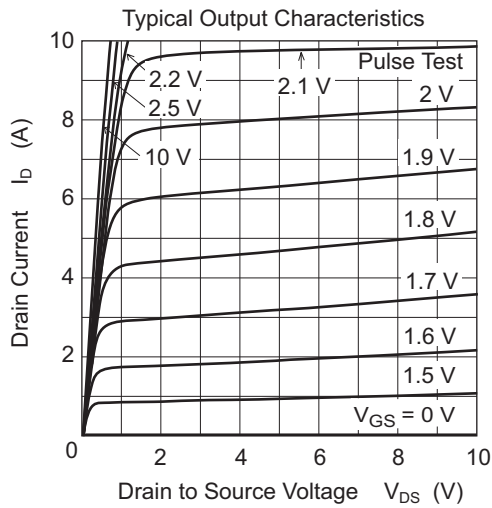
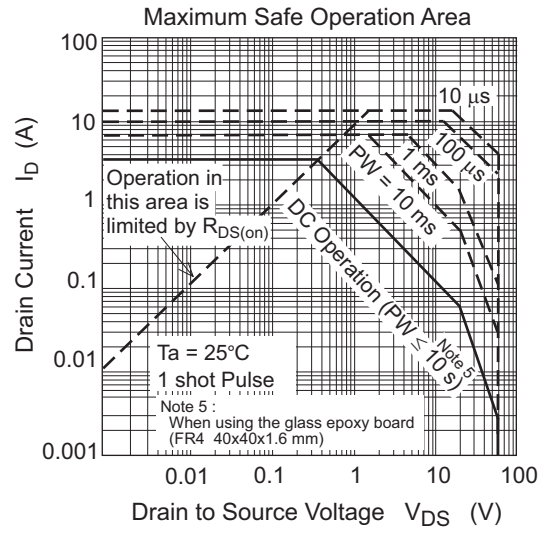
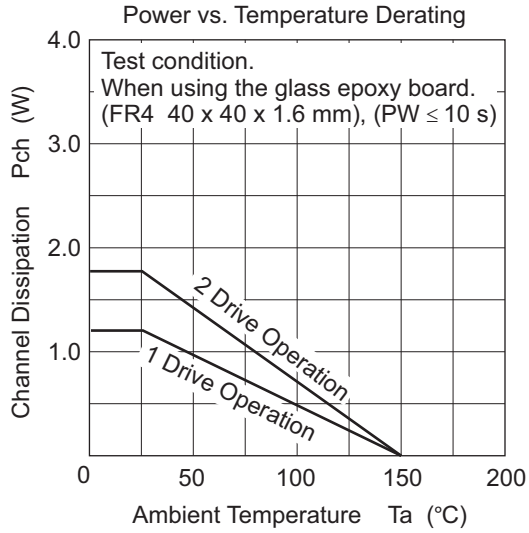
Electrical Characteristics

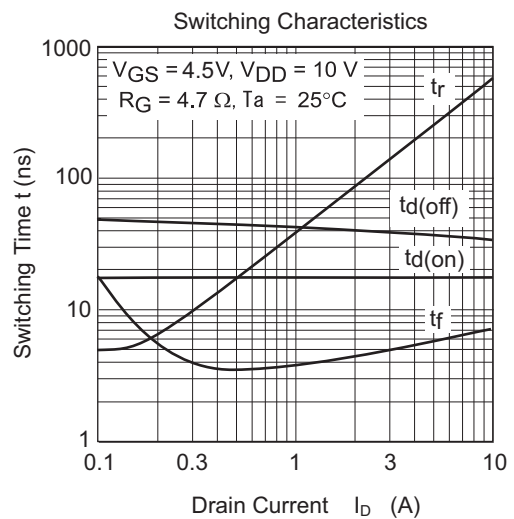
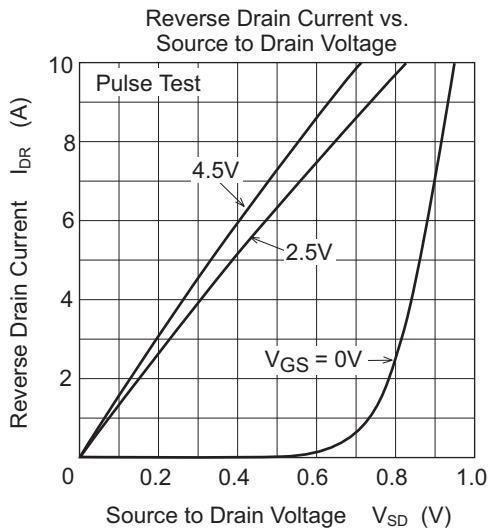
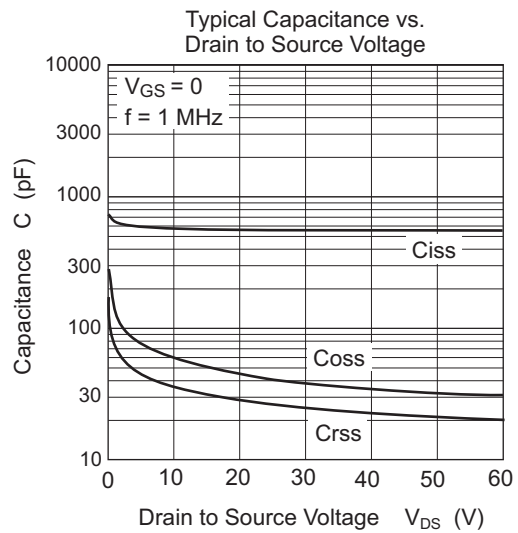
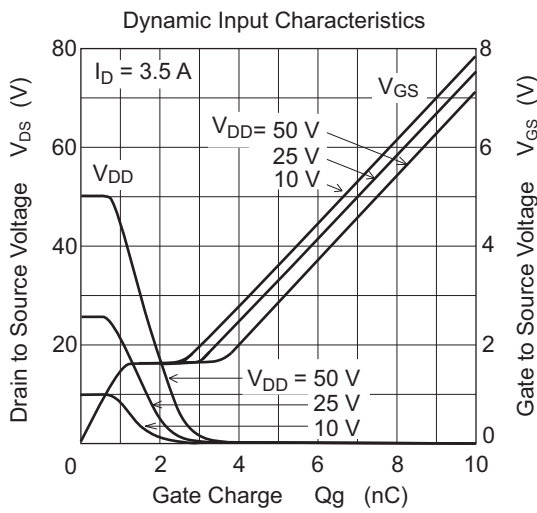
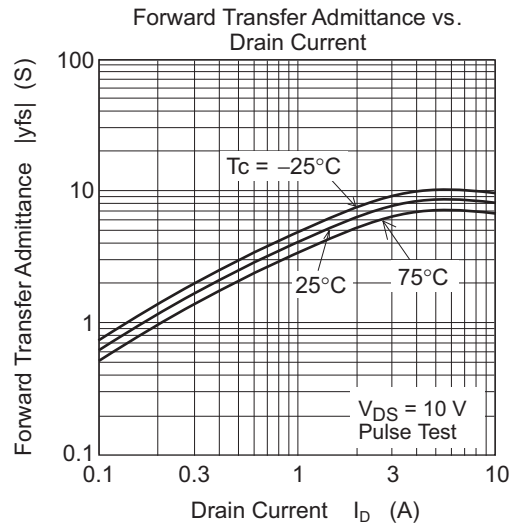
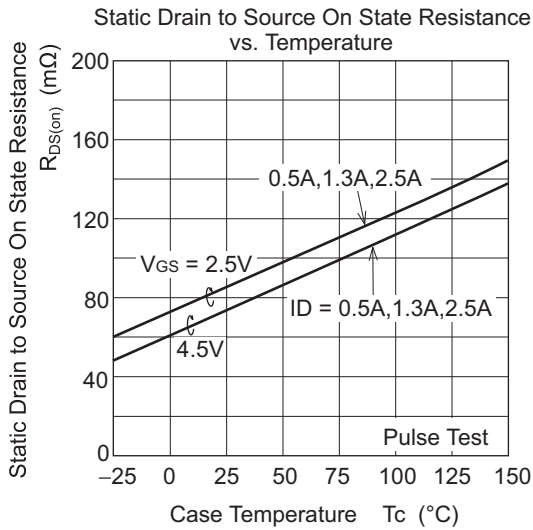
(Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|--------------------------------------------|---------------|----------|------|----------|---------------|------------------------------------------------------------------------------------------------------------------------------------------------|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 60 | — | — | V | $I_D = 10 \text{ mA}$, $V_{GS} = 0$ |
| Gate to source breakdown voltage | $V_{(BR)GSS}$ | ± 12 | — | — | V | $I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$ |
| Gate to source leak current | I_{GSS} | — | — | ± 10 | μA | $V_{GS} = \pm 10 \text{ V}$, $V_{DS} = 0$ |
| Zero gate voltage drain current | I_{DSS} | — | — | 1 | μA | $V_{DS} = 60 \text{ V}$, $V_{GS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 0.4 | — | 1.4 | V | $V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$ |
| Static drain to source on state resistance | $R_{DS(on)}$ | — | 75 | 98 | m Ω | $I_D = 1.75 \text{ A}$, $V_{GS} = 4.5 \text{ V}$ ^{Note5} |
| | $R_{DS(on)}$ | — | 85 | 119 | m Ω | $I_D = 1.75 \text{ A}$, $V_{GS} = 2.5 \text{ V}$ ^{Note5} |
| Forward transfer admittance | $ y_{fs} $ | 6 | 10 | — | S | $I_D = 1.75 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note5} |
| Input capacitance | C_{iss} | — | 590 | — | pF | $V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$ |
| Output capacitance | C_{oss} | — | 60 | — | pF | |
| Reverse transfer capacitance | C_{rss} | — | 35 | — | pF | |
| Total gate charge | Q_g | — | 6 | — | nc | $V_{DD} = 10 \text{ V}$, $V_{GS} = 4.5 \text{ V}$, $I_D = 3.5 \text{ A}$ |
| Gate to source charge | Q_{gs} | — | 1.2 | — | nc | |
| Gate to drain charge | Q_{gd} | — | 1.4 | — | nc | |
| Turn-on delay time | $t_{d(on)}$ | — | 17 | — | ns | $V_{GS} = 10 \text{ V}$, $I_D = 1.75 \text{ A}$, $V_{DD} \cong 10 \text{ V}$, $R_L = 5.7 \text{ }\Omega$, $R_g = 4.7 \text{ }\Omega$ |
| Rise time | t_r | — | 70 | — | ns | |
| Turn-off delay time | $t_{d(off)}$ | — | 41 | — | ns | |
| Fall time | t_f | — | 4.2 | — | ns | |
| Body-drain diode forward voltage | V_{DF} | — | 0.81 | 1.06 | V | $I_F = 3.5 \text{ A}$, $V_{GS} = 0$ ^{Note5} |
| Body-drain diode reverse recovery time | t_{rr} | — | 20 | — | ns | $I_F = 3.5 \text{ A}$, $V_{GS} = 0 \text{ V}$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ |

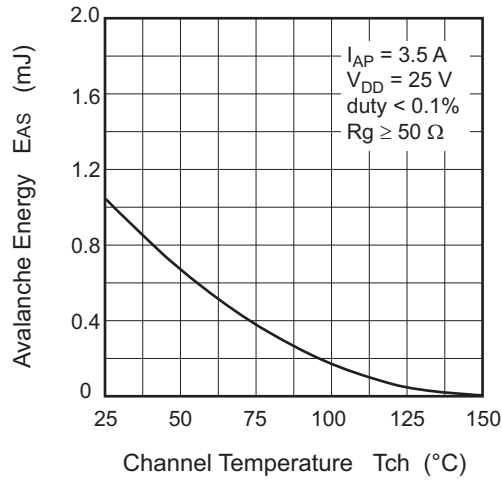
Notes: 5. Pulse test

Main Characteristics

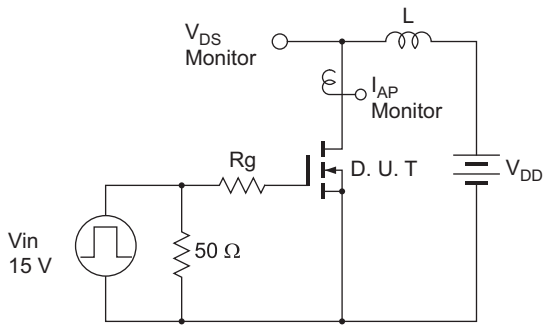




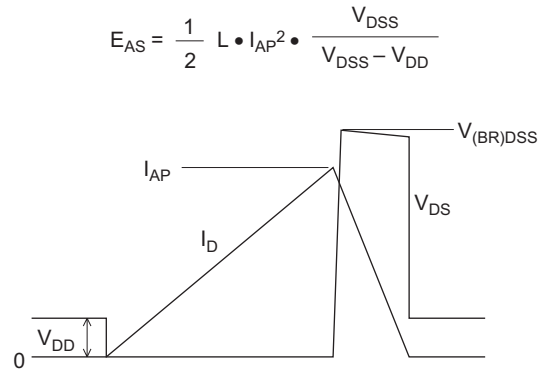
Maximum Avalanche Energy vs. Channel Temperature Derating

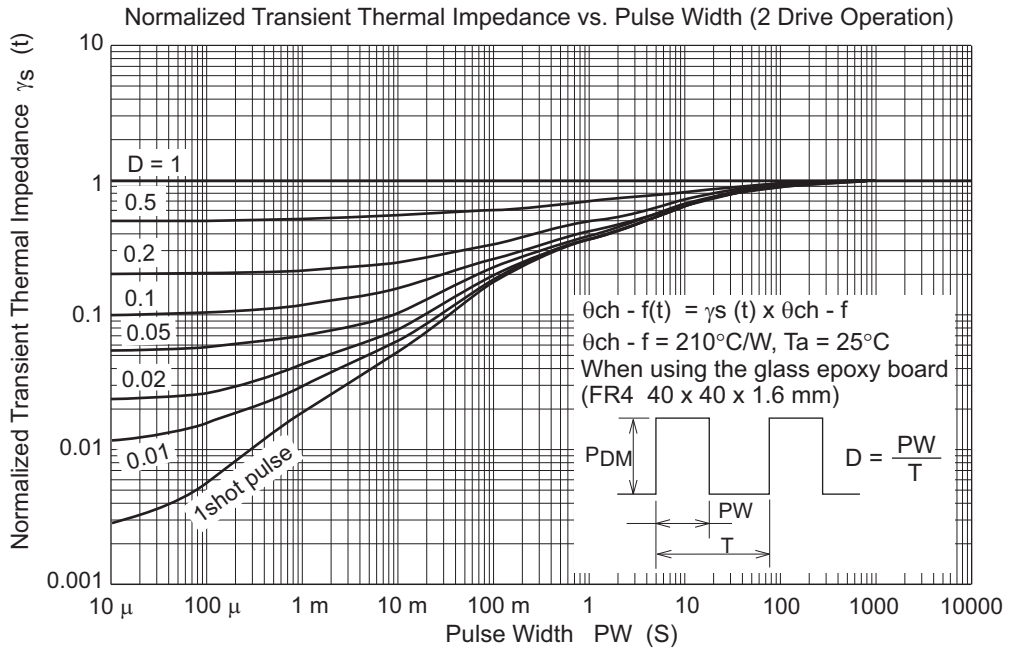
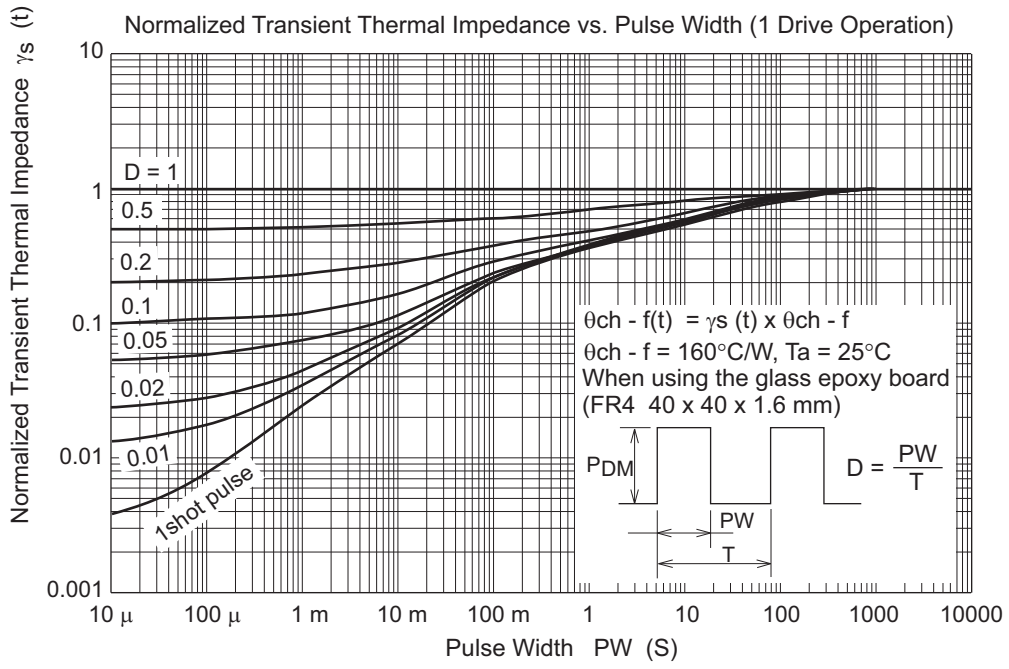


Avalanche Test Circuit

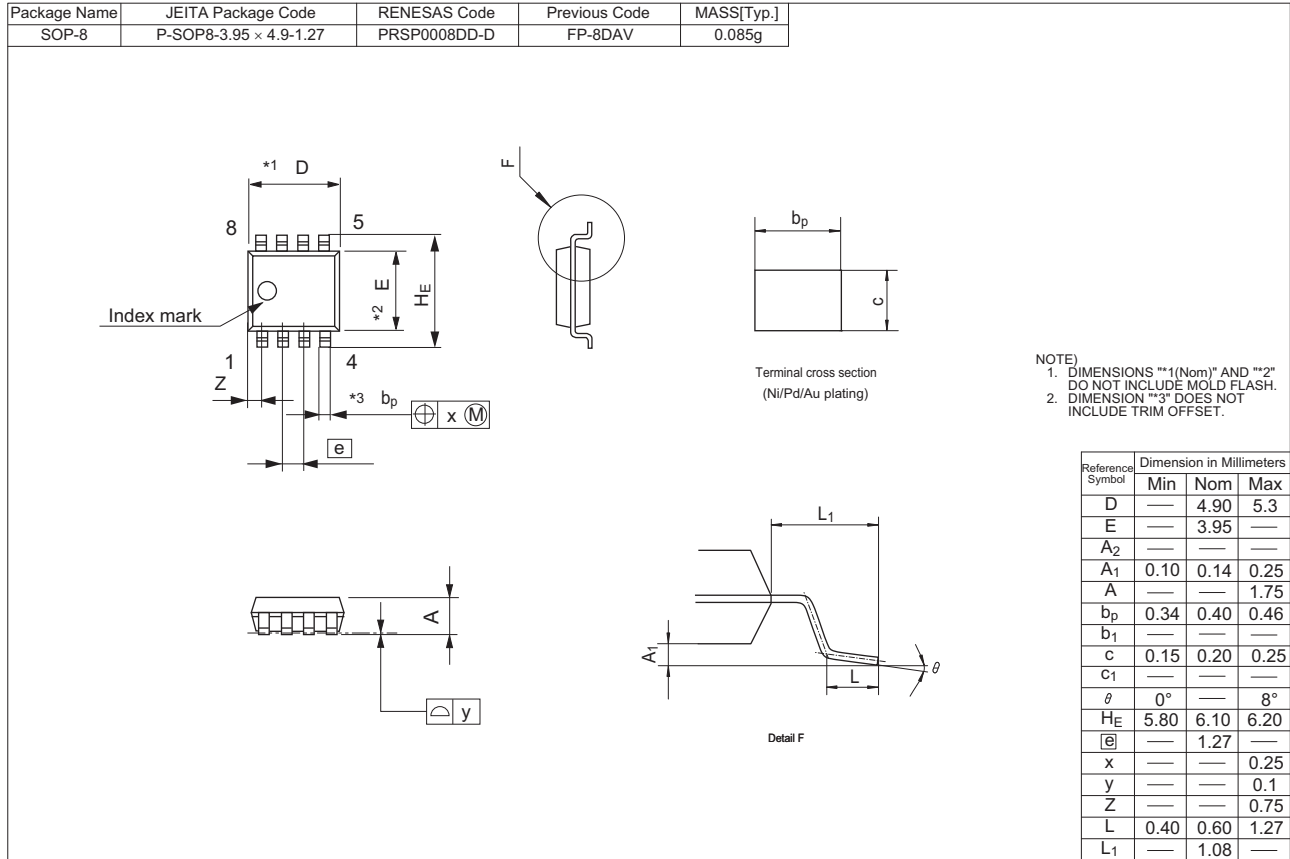


Avalanche Waveform





Package Dimensions



Ordering Information

| Orderable Part Number | Quantity | Shipping Container |
|-----------------------|----------|--------------------|
| RJK0635DSP-00-J0 | 2500 pcs | Taping |

Note: The symbol of 2nd "-" is occasionally presented as "#".

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